



# TSM6866SD

## 20V Dual N-Channel MOSFET

#### TSSOP-8

#### Pin Definition:

1

1. Drain 1 8. Drain 2 2. Source 1 7. Source 2 3. Source 1 6. Source 2 4. Gate 1 5. Gate 2

#### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)	
20	30 @ V <sub>GS</sub> = 4.5V	6.0	
	40 @ V <sub>GS</sub> = 2.5V	5.2	

#### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

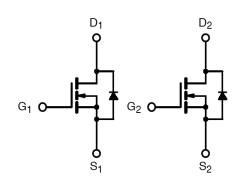
#### **Application**

- Specially Designed for Li-on Battery Packs
- Battery Switch Application

#### **Ordering Information**

Part No.	Package	Packing
TSM6866SDCA RV	TSSOP-8	3Kpcs / 13" Reel

#### **Block Diagram**



**Dual N-Channel MOSFET** 

### **Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter	ameter		Limit	Unit
Drain-Source Voltage		$V_{DS}$	20	V
Gate-Source Voltage		$V_{GS}$	±12	V
Continuous Drain Current		I <sub>D</sub>	6	А
Pulsed Drain Current		I <sub>DM</sub>	30	А
Continuous Source Current (Diode Co	onduction) <sup>a,b</sup>	I <sub>S</sub>	1.7	А
Maximum Dawar Dissination	Ta = 25°C	- P <sub>D</sub>	1.6	
Maximum Power Dissipation	Ta = 75°C		1.1	W
Operating Junction Temperature		TJ	+150	°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit			
Junction to Case Thermal Resistance	RO <sub>JC</sub>	30	°C/W			
Junction to Ambient Thermal Resistance (PCB mounted)	RO <sub>JA</sub>	62.5	°C/W			

#### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board,  $t \le 5$  sec.



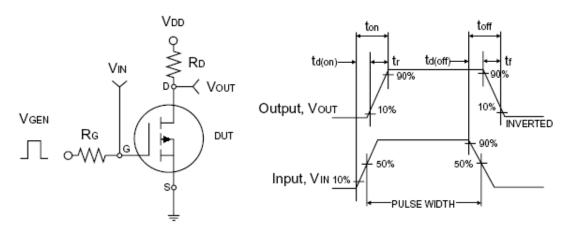


**Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static					•	
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV <sub>DSS</sub>	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	0.6			V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I <sub>GSS</sub>	1		±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I <sub>DSS</sub>	1		1.0	uA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I <sub>D(ON)</sub>	30			Α
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 6.0A$	В	1	21	30	mΩ
Dialii-Source Oii-State Resistance	$V_{GS} = 2.5V, I_D = 5.2A$	R <sub>DS(ON)</sub>	1	30	40	
Forward Transconductance	$V_{DS} = 10V, I_D = 6A$	g <sub>fs</sub>	1	30		S
Diode Forward Voltage	$I_{S} = 1.7A, V_{GS} = 0V$	$V_{SD}$		0.7	1.2	V
Dynamic <sup>b</sup>		_				
Total Gate Charge	$V_{DS} = 10V, I_D = 6A,$	$Q_g$		5	7	
Gate-Source Charge	$V_{DS} = 10V, I_D = 0A,$ - $V_{GS} = 4.5V$	$Q_gs$		1		nC
Gate-Drain Charge	V <sub>GS</sub> = 4.5 V	$Q_{gd}$		1.5		
Input Capacitance	\/ - 0\/ \/ - 0\/	C <sub>iss</sub>		565		
Output Capacitance	$V_{DS} = 8V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>oss</sub>		105		pF
Reverse Transfer Capacitance	1 - 1.0101112	C <sub>rss</sub>	-	75		
Switching <sup>c</sup>						
Turn-On Delay Time	V = 40V D = 400	t <sub>d(on)</sub>	-	8	20	
Turn-On Rise Time	$V_{DD} = 10V, R_L = 10\Omega,$ $I_D = 1A, V_{GEN} = 4.5V,$	t <sub>r</sub>	-	10	20	nS
Turn-Off Delay Time	$I_D = IA$ , $V_{GEN} = 4.5V$ , - $R_G = 6\Omega$	$t_{d(off)}$	-	22	45	110
Turn-Off Fall Time	17G - 075	t <sub>f</sub>		6	15	

#### Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

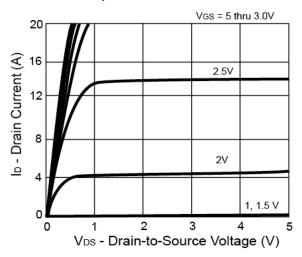
Switchin Waveforms



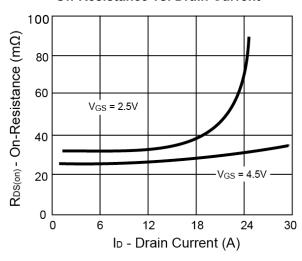


#### **Electrical Characteristics Curve** (Ta = 25°C, unless otherwise noted)

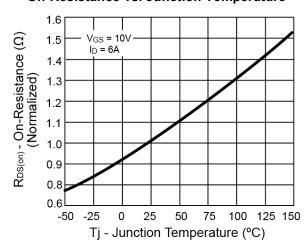
#### **Output Characteristics**



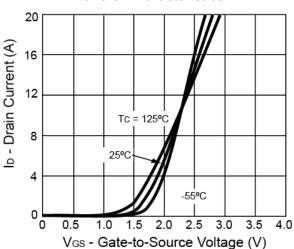
#### **On-Resistance vs. Drain Current**



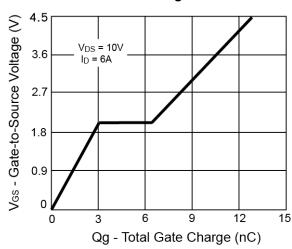
#### On-Resistance vs. Junction Temperature



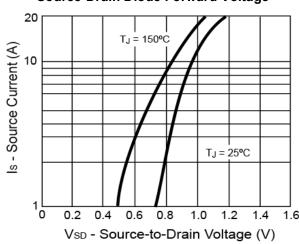
#### **Transfer Characteristics**



#### Gate Charge



#### **Source-Drain Diode Forward Voltage**



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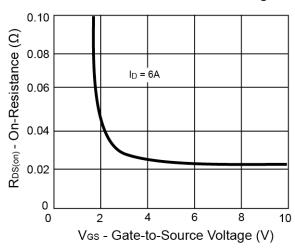
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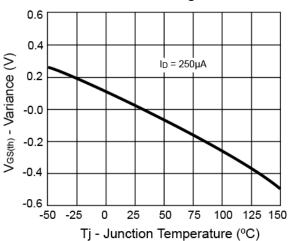


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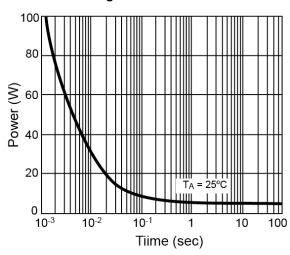
#### On-Resistance vs. Gate-Source Voltage



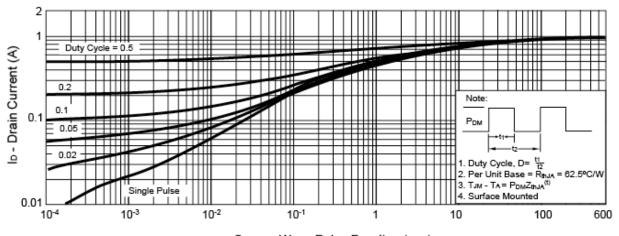
## Threshold Voltage



#### **Single Pulse Power**



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



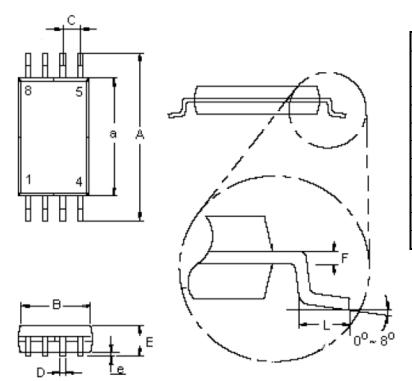
Square Wave Pulse Duration (sec)

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## **TSSOP-8 Mechanical Drawing**



TSSOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
Α	6.20	6.60	0.244	0.260	
а	4.30	4.50	0.170	0.177	
В	2.90	3.10	0.114	0.122	
С	0.65 (typ)		0.025 (typ)		
D	0.25	0.30	0.010	0.019	
Е	1.05	1.20	0.041	0.049	
е	0.05	0.15	0.002	0.009	
F	0.127		0.005		
L	0.50	0.70	0.020	0.028	

## **Marking Diagram**



Y = Year Code

**M** = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



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